

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_C = +25^\circ C$
30V	9.5m Ω @ $V_{GS} = 10V$	43A
	11.5m Ω @ $V_{GS} = 4.5V$	39A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- DC-DC Converters
- Power Management Functions

Features

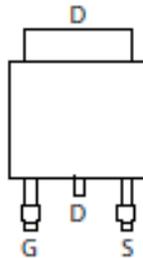
- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

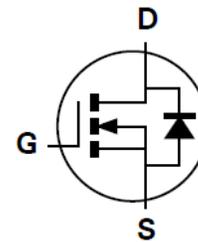
- Case: TO252-3L
- Case Material: Molded Plastic, “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.33 grams (approximate)



Top View



Pin Out Top View



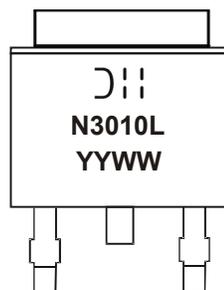
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3010LK3-13	TO252	2500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



= Manufacturer's Marking
 N3010L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 13 = 2013)
 WW = Week Code (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_C = +25^\circ\text{C}$ $T_C = +70^\circ\text{C}$	I_D	43 34	A
	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	13.1 10.5	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	90	A
Avalanche Current (Notes 7) $L = 0.1\text{mH}$			I_{AR}	28	A
Avalanche Energy (Notes 7) $L = 0.1\text{mH}$			E_{AR}	40	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_D	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	78	$^\circ\text{C/W}$
	$t < 10\text{s}$		31	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)		P_D	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	51	$^\circ\text{C/W}$
	$t < 10\text{s}$		21	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	4.7	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	8	9.5	m Ω	$V_{GS} = 10\text{V}, I_D = 18\text{A}$
		—	10	11.5		$V_{GS} = 4.5\text{V}, I_D = 16\text{A}$
Diode Forward Voltage	V_{SD}	—	0.75	1.0	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	2075	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	190	—		
Reverse Transfer Capacitance	C_{rss}	—	138	—		
Gate resistance	R_g	—	2.4	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	16.1	—	nC	$V_{DS} = 15\text{V}, I_D = 18\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	37	—		
Gate-Source Charge	Q_{gs}	—	6.1	—		
Gate-Drain Charge	Q_{gd}	—	5.9	—		
Turn-On Delay Time	$t_{D(on)}$	—	4.5	—	ns	$V_{DS} = 15\text{V}, V_{GS} = 10\text{V}, R_L = 0.83\Omega, R_{GEN} = 3\Omega,$
Turn-On Rise Time	t_r	—	19.6	—		
Turn-Off Delay Time	$t_{D(off)}$	—	31	—		
Turn-Off Fall Time	t_f	—	10.7	—		
Reverse Recovery Time	t_{rr}	—	13.7	—	ns	$I_F = 15\text{A}, di/dt = 500\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{rr}	—	18.3	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

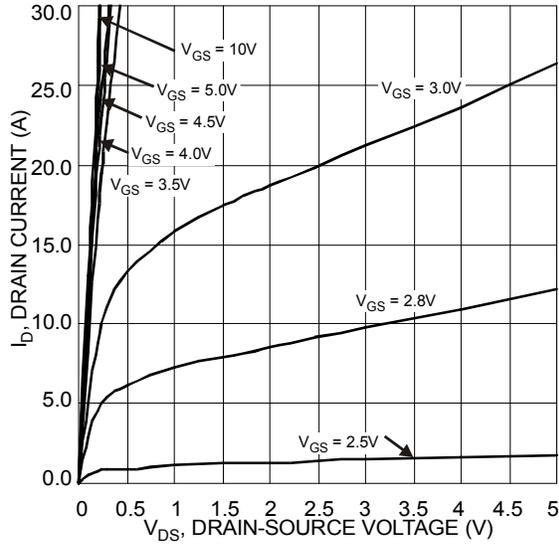


Figure 1 Typical Output Characteristic

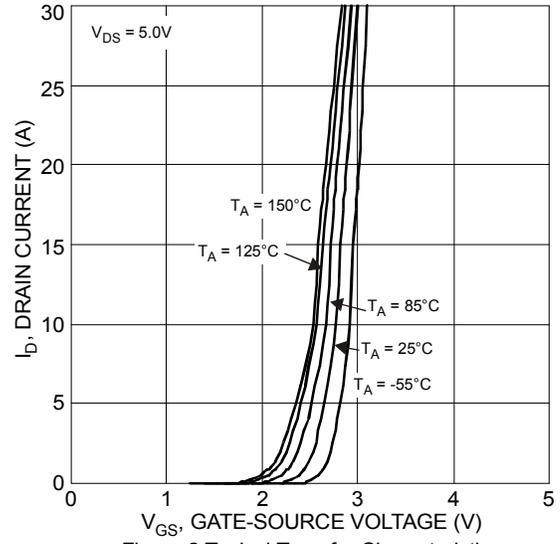


Figure 2 Typical Transfer Characteristics

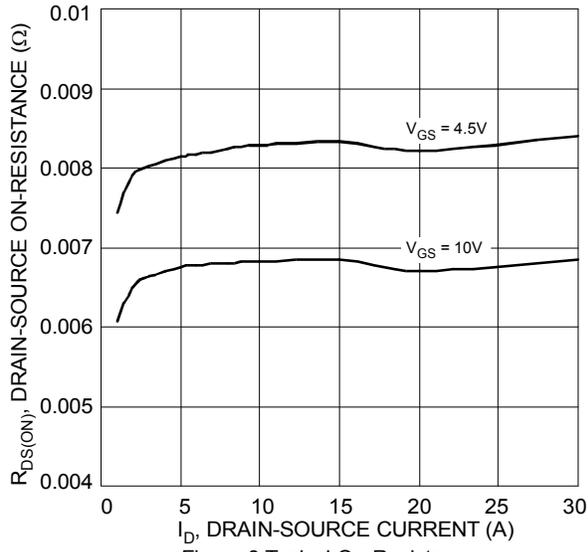


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

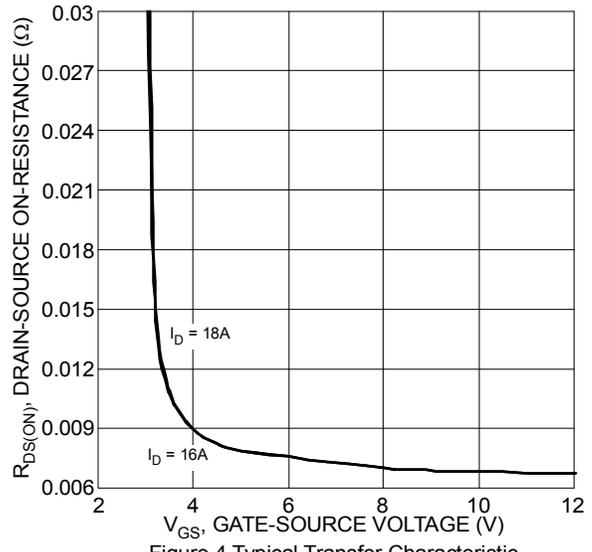


Figure 4 Typical Transfer Characteristic

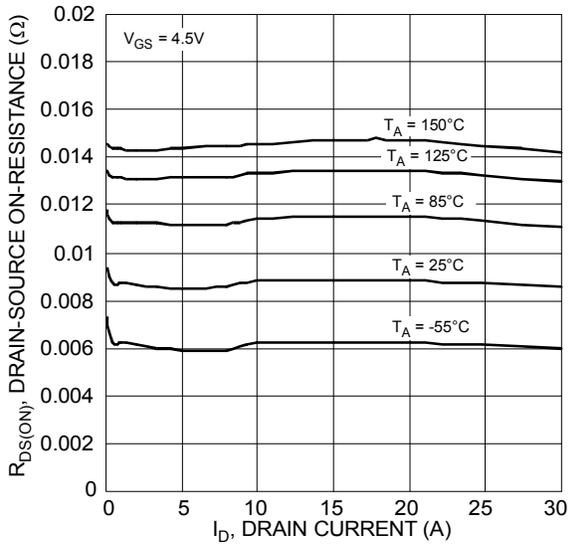


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

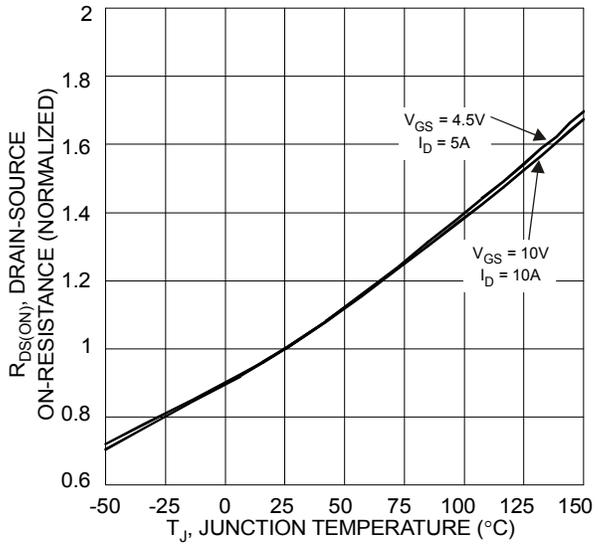
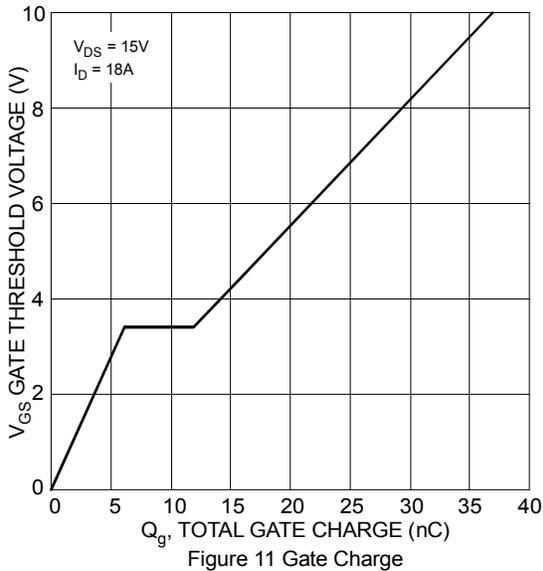
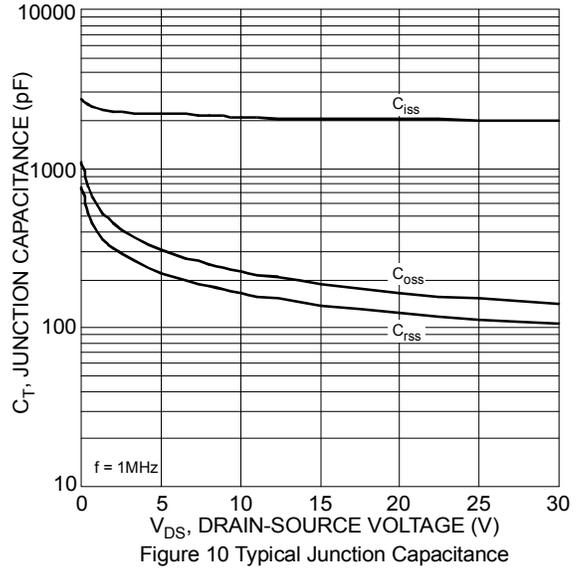
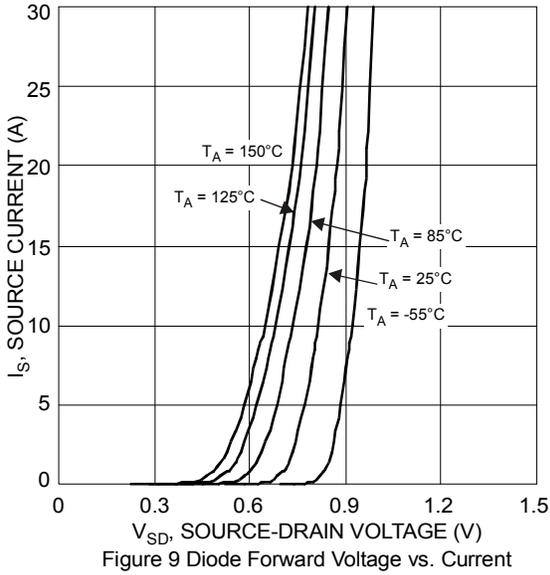
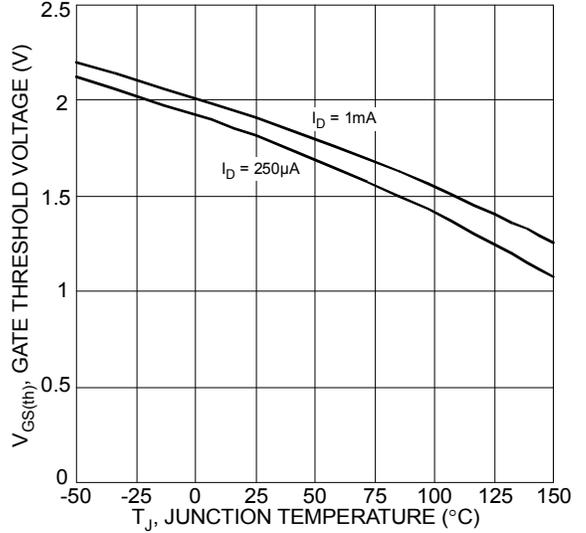
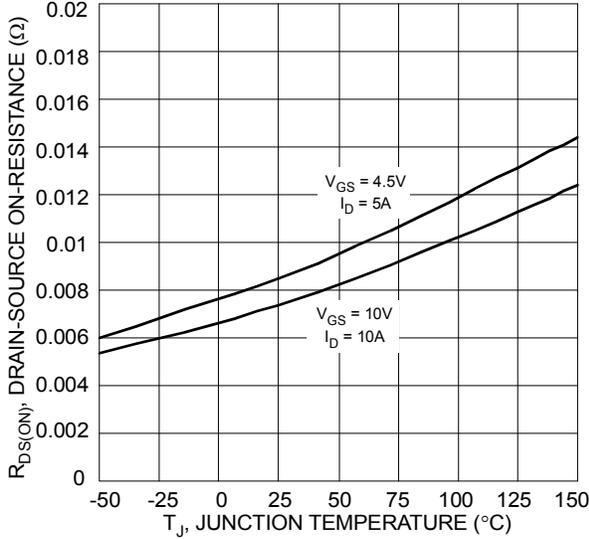


Figure 6 On-Resistance Variation with Temperature



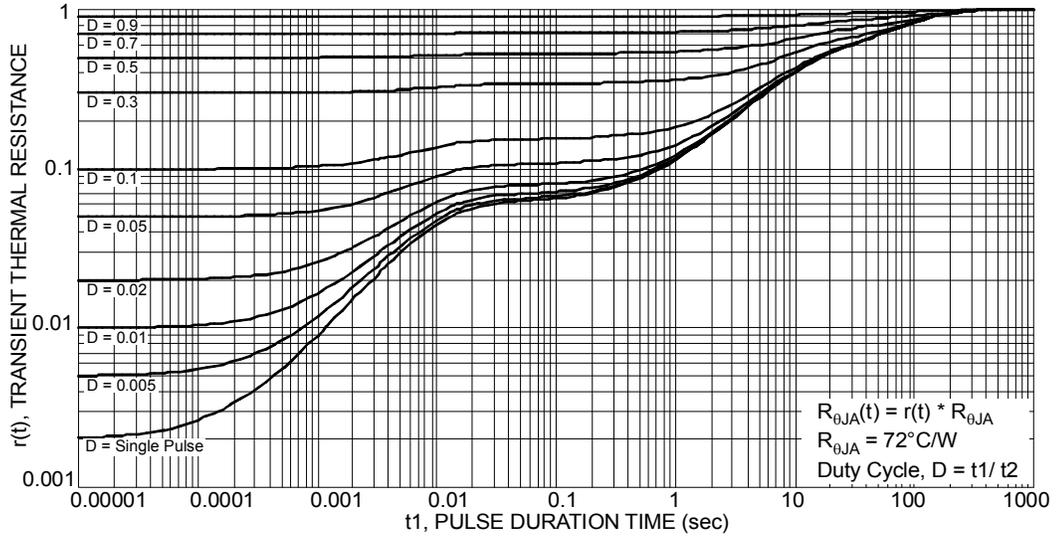
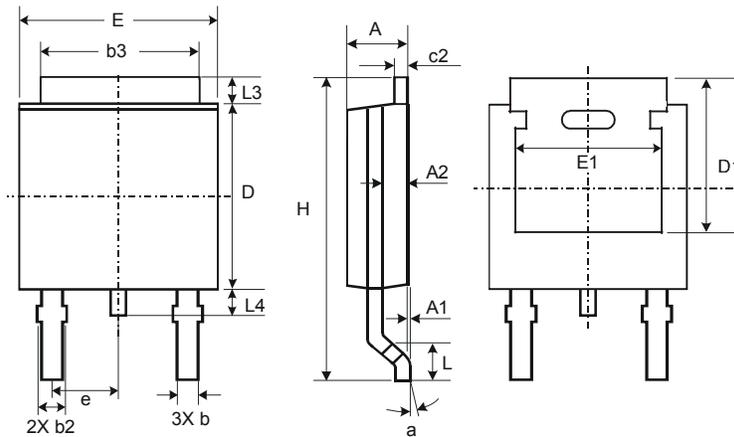


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

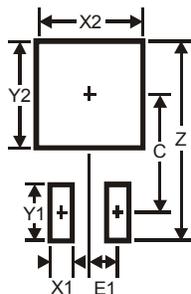
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	–	–
e	–	–	2.286
E	6.45	6.70	6.58
E1	4.32	–	–
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	–
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3

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